

TO-252-2L Plastic-Encapsulate Transistors

MJD3055 TRANSISTOR (NPN)

FEATURES

- Designed for General Purpose Amplifier and Low Speed Switching Applications
- Electrically Similar to MJE3055
- DC Current Gain Specified to 10 Amperes

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

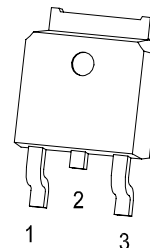
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	70	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	10	A
P _C	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-252-2L

1.BASE

2.COLLECTOR

3.EMITTER



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =1mA, I _E =0	70			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =200 mA, I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =70V, I _E =0			0.02	mA
	I _{CEO}	V _{CB} =30V, I _B =0			50	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.5	mA
DC current gain	h _{FE(1)}	V _{CE} =4V, I _C =4A	20		100	
	h _{FE(2)}	V _{CE} =4V, I _C =10A	5			
Collector-emitter saturation voltage	V _{CE(sat)(1)}	I _C =4A, I _B =0.4A			1.1	V
	V _{CE(sat)(2)}	I _C =10A, I _B =3.3A			8	V
Base-emitter voltage	V _{BE}	V _{CE} =4V, I _C =4A			1.8	V
Transition frequency	f _T	V _{CE} =10V, I _C =0.5A, f=500KHz	2			MHz

Static Characteristic

